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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8360czuagdga

- Eight TDM interfaces on the MPC8360E and four TDM interfaces on the MPC8358E with 1-bit mode for E3/T3 rates in clear channel
- Sixteen independent baud rate generators and 30 input clock pins for supplying clocks to UCC and MCC serial channels (MCC is only available on the MPC8360E)
- Four independent 16-bit timers that can be interconnected as four 32-bit timers
- Interworking functionality:
  - Layer 2 10/100-Base T Ethernet switch
  - ATM-to-ATM switching (AAL0, 2, 5)
  - Ethernet-to-ATM switching with L3/L4 support
  - PPP interworking

- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs).
  - Public key execution unit (PKEU) supporting the following:
    - RSA and Diffie-Hellman
    - Programmable field size up to 2048 bits
    - Elliptic curve cryptography
    - F2m and F(p) modes
    - Programmable field size up to 511 bits
  - Data encryption standard execution unit (DEU)
    - DES, 3DES
    - Two key (K1, K2) or three key (K1, K2, K3)
    - ECB and CBC modes for both DES and 3DES
  - Advanced encryption standard unit (AESU)
  - Implements the Rinjdael symmetric key cipher
  - Key lengths of 128, 192, and 256 bits, two key
    - ECB, CBC, CCM, and counter modes
  - ARC four execution unit (AFEU)
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - Message digest execution unit (MDEU)
    - SHA with 160-, 224-, or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either SHA or MD5 algorithm
  - Random number generator (RNG)
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Static and/or dynamic assignment of crypto-execution units via an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - Storage/NAS XOR parity generation accelerator for RAID applications
- Dual DDR SDRAM memory controllers on the MPC8360E and a single DDR SDRAM memory controller on the MPC8358E
  - Programmable timing supporting both DDR1 and DDR2 SDRAM
  - On the MPC8360E, the DDR buses can be configured as two 32-bit buses or one 64-bit bus; on the MPC8358E, the DDR bus can be configured as a 32- or 64-bit bus
  - 32- or 64-bit data interface, up to 333 MHz (for the MPC8360E) and 266 MHz (for the MPC8358E) data rate
  - Four banks of memory, each up to 1 Gbyte

Table 1. Absolute Maximum Ratings[1] (continued)

Characteristic	Symbol	Max Value	Unit	Notes
Storage temperature range	T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution: M**V_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 3.
6. OV_{IN} on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 4.

2.1.2 Power Supply Voltage Specification

This table provides the recommended operating conditions for the device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Core and PLL supply voltage for MPC8358 Device Part Number with Processor Frequency label of AD=266MHz and AG=400MHz & QUICC Engine Frequency label of E=300MHz & G=400MHz MPC8360 Device Part Number with Processor Frequency label of AG=400MHz and AJ=533MHz & QUICC Engine Frequency label of G=400MHz	V_{DD} & AV_{DD}	1.2 V ± 60 mV	V	1, 3
Core and PLL supply voltage for MPC8360 Device Part Number with Processor Frequency label of AL=667MHz and QUICC Engine Frequency label of H=500MHz	V_{DD} & AV_{DD}	1.3 V ± 50 mV	V	1, 3
DDR and DDR2 DRAM I/O supply voltage DDR DDR2	GV_{DD}	 2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O supply voltage	$LV_{DD}0$	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	$LV_{DD}1$	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	$LV_{DD}2$	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—

Table 9. GTX_CLK125 AC Timing Specifications

At recommended operating conditions with LV_{DD} = 2.5 ± 0.125 mV/ 3.3 V ± 165 mV (continued)

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
GTX_CLK rise and fall time LV_{DD} = 2.5 V LV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
GTX_CLK125 duty cycle GMII & TBI 1000Base-T for RGMII & RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2
GTX_CLK125 jitter	—	—	—	±150	ps	2

Notes:

1. Rise and fall times for GTX_CLK125 are measured from 0.5 and 2.0 V for LV_{DD} = 2.5 V and from 0.6 and 2.7 V for LV_{DD} = 3.3 V.
2. GTX_CLK125 is used to generate the GTX clock for the UCC Ethernet transmitter with 2% degradation. The GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by GTX_CLK. See Section 8.2.2, “MII AC Timing Specifications,” Section 8.2.3, “RMII AC Timing Specifications,” and Section 8.2.5, “RGMII and RTBI AC Timing Specifications” for the duty cycle for 10Base-T and 100Base-T reference clock.

5 RESET Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8360E/58E.

5.1 RESET DC Electrical Characteristics

This table provides the DC electrical characteristics for the RESET pins of the device.

Table 10. RESET Pins DC Electrical Characteristics [1]

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±10	μA
Output high voltage	V_{OH}[2]	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:

1. This table applies for pins $\overline{\text{PORESET}}$, $\overline{\text{HRESET}}$, $\overline{\text{SRESET}}$, and $\overline{\text{QUIESCE}}$.
2. $\overline{\text{HRESET}}$ and $\overline{\text{SRESET}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.125	V	—
Output leakage current	I_{OZ}	—	±10	µA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	µA	—
Input current (0 V ≤ V_{IN} ≤ GV_{DD})	I_{IN}	—	±10	µA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to equal 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

This table provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 15. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the device when GV_{DD}(typ) = 2.5 V.

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8360E/58E.

7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface of the device.

Table 23. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage OV_{DD}	V_{IL}	–0.3	0.8	V	—
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.4	—	V	—
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V	—
Input current (0 V ≤V_{IN} ≤OV_{DD})	I_{IN}	—	±10	µA	1

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface of the device.

Table 24. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	—
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

Notes:

1. Actual attainable baud rate is limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the eighth sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each sixteenth sample.

8 UCC Ethernet Controller: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speed, 10/100/1000, and MII management.

8.1 Three-Speed Ethernet Controller (10/100/1000 Mbps)— GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to all GMII (gigabit media independent interface), MII (media independent interface), RMII (reduced media independent interface), TBI (ten-bit interface), RGMII (reduced gigabit media independent interface), and RTBI (reduced ten-bit interface) signals except MDIO (management data input/output) and MDC (management data clock). The MII, RMII, GMII, and TBI interfaces are only defined for 3.3 V, while the RGMII and RTBI interfaces are only defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard reduced pin-count interface for Gigabit Ethernet

Table 32. RMII Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK	$t_{RMRDVKH}$	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK	$t_{RMRDXKH}$	2.0	—	—	ns
REF_CLK clock rise time	t_{RMXR}	1.0	—	4.0	ns
REF_CLK clock fall time	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMRDVKH}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, $t_{RMRDXKL}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) went invalid (X) relative to the t_{RMX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load.

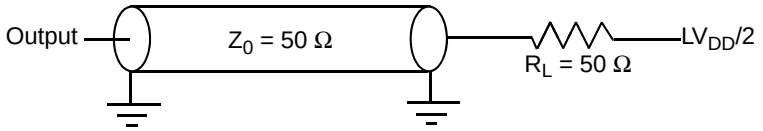

Figure 16. AC Test Load

This figure shows the RMII receive AC timing diagram.

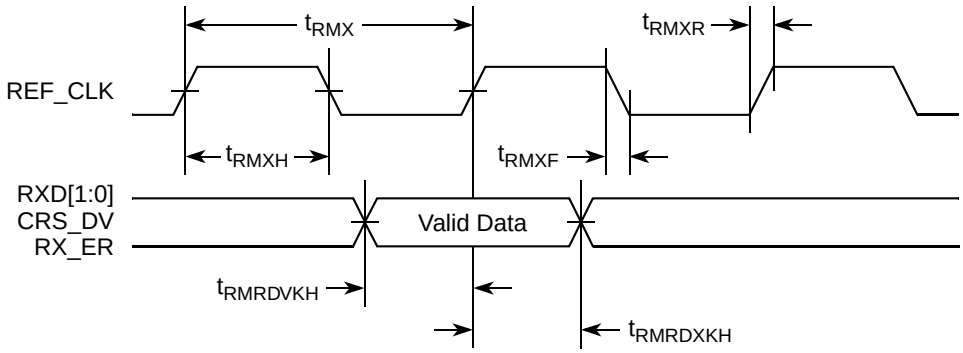

Figure 17. RMII Receive AC Timing Diagram

8.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

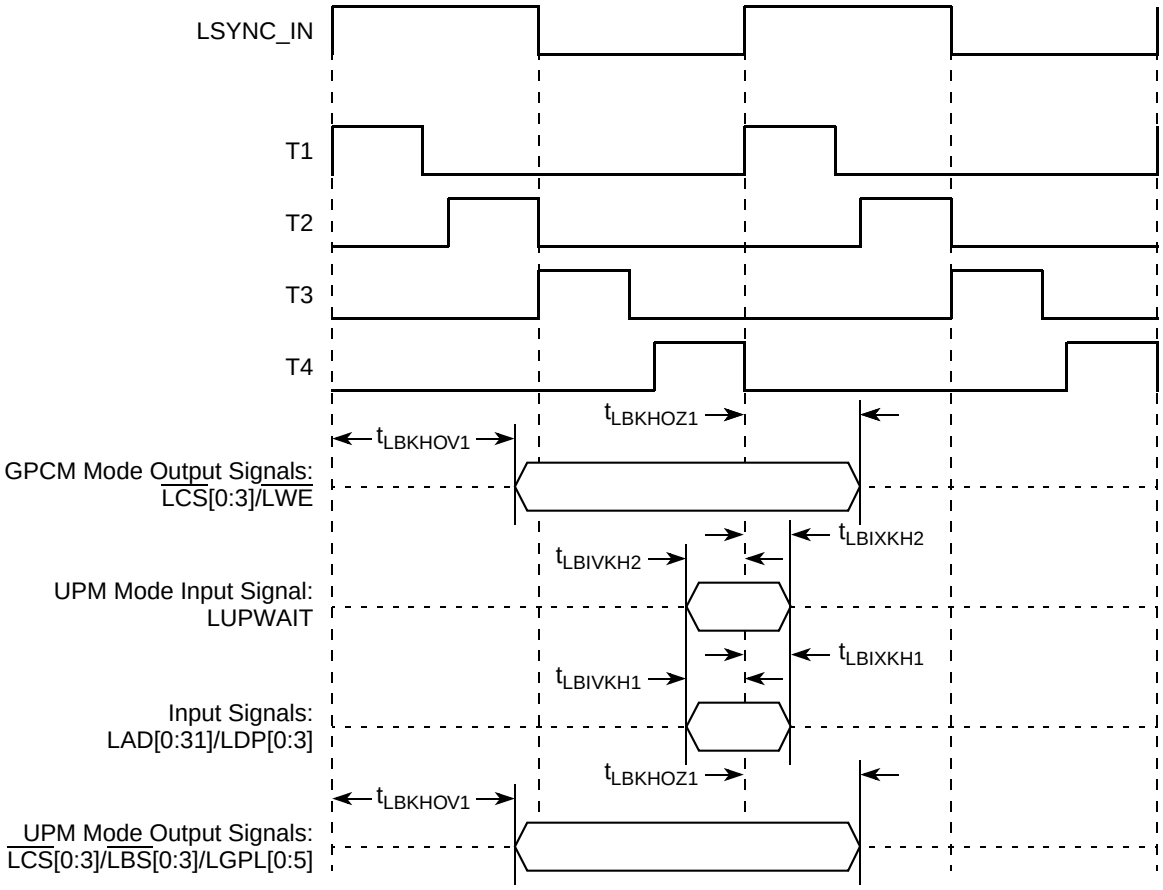

Figure 28. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (DLL Enabled)

10 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8360E/58E.

10.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the IEEE 1149.1 (JTAG) interface of the device.

Table 42. JTAG interface DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.5	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤V_{IN} ≤OV_{DD}	—	±10	μA

This figure provides the test access port timing diagram.

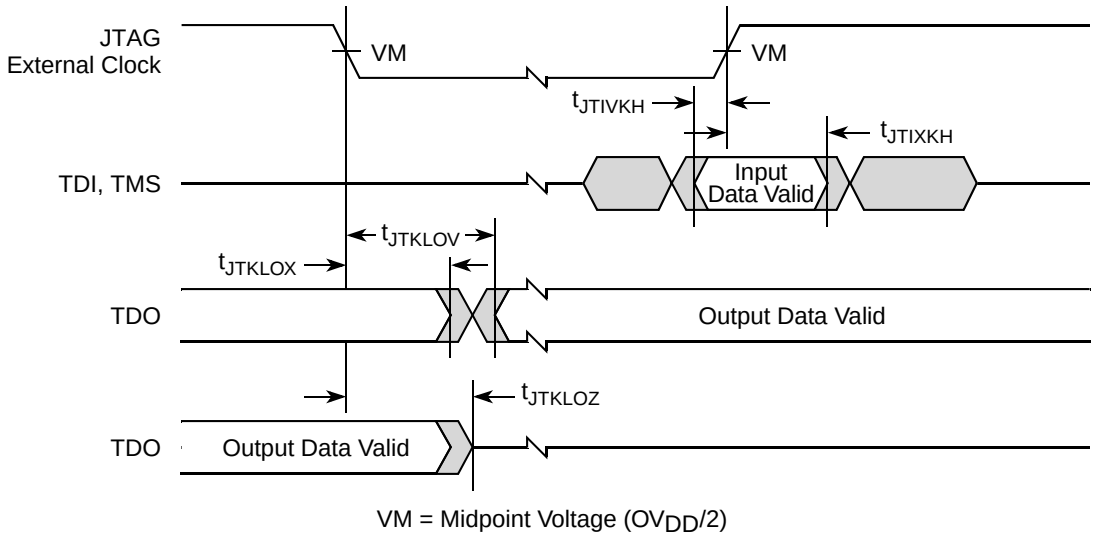

Figure 33. Test Access Port Timing Diagram

11 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8360E/58E.

11.1 I²C DC Electrical Characteristics

This table provides the DC electrical characteristics for the I²C interface of the device.

Table 44. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	0.7 × OV_{DD}	OV_{DD} + 0.3	V	—
Input low voltage level	V_{IL}	–0.3	0.3 × OV_{DD}	V	—
Low level output voltage	V_{OL}	0	0.4	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	20 + 0.1 × C_B	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Capacitance for each I/O pin	C_I	—	10	pF	—
Input current (0 V ≤V_{IN} ≤OV_{DD})	I_{IN}	—	±10	μA	4

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8360E Integrated Communications Processor Reference Manual* for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

This figure provides the AC test load for the I^2C.

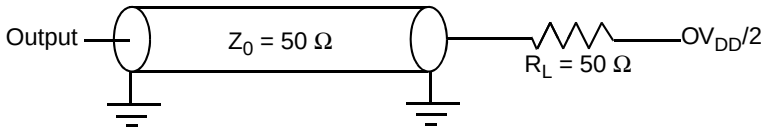

Figure 34. I^2C AC Test Load

This figure shows the AC timing diagram for the I^2C bus.

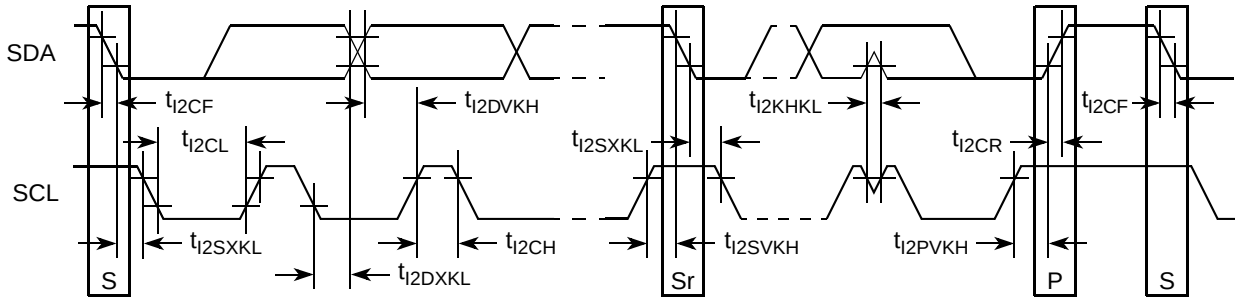

Figure 35. I^2C Bus AC Timing Diagram

12 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8360E/58E.

12.1 PCI DC Electrical Characteristics

This table provides the DC electrical characteristics for the PCI interface of the device.

Table 46. PCI DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	$0.5 \times OV_{DD}$	$OV_{DD} + 0.5$	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	-0.5	$0.3 \times OV_{DD}$	V
High-level output voltage	V_{OH}	I_{OH} = –500 µA	$0.9 \times OV_{DD}$	—	V
Low-level output voltage	V_{OL}	I_{OL} = 1500 µA	—	$0.1 \times OV_{DD}$	V
Input current	I_{IN}	$0 V \leq V_{IN}$[1] $\leq OV_{DD}$	—	±10	µA

12.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus of the device. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the device is configured as a host or agent device. This table provides the PCI AC timing specifications at 66 MHz.

Table 47. PCI AC Timing Specifications at 66 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	6.0	ns	2, 5
Output hold from clock	t_{PCKHOX}	1	—	ns	2

Table 47. PCI AC Timing Specifications at 66 MHz (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0.3	—	ns	2, 4, 6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.
5. In rev. 2.0 silicon, due to errata, t_{PCIHOV} maximum is 6.6 ns. Refer to Errata PCI21 in *Chip Errata for the MPC8360E, Rev. 1*.
6. In rev. 2.0 silicon, due to errata, t_{PCIXKH} minimum is 1 ns. Refer to Errata PCI17 in *Chip Errata for the MPC8360E, Rev. 1*.

Table 48. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	7.0	—	ns	2, 2
Input hold from clock	t_{PCIXKH}	0.3	—	ns	2, 4, 5

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.
5. In rev. 2.0 silicon, due to errata, t_{PCIXKH} minimum is 1 ns. Refer to Errata PCI17 in *Chip Errata for the MPC8360E, Rev. 1*.

This figure provides the AC test load for PCI.

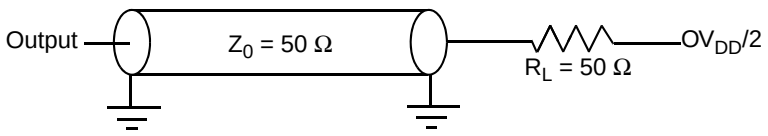

Figure 36. PCI AC Test Load

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 63. Synchronous UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

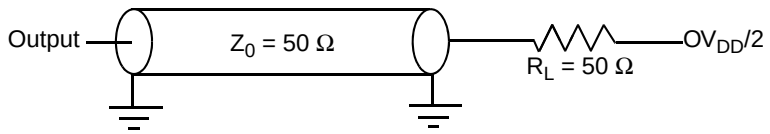

Figure 49. AC Test Load

20 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8360E/58E is available in a tape ball grid array (TBGA), see Section 20.1, “Package Parameters for the TBGA Package,” and Section 20.2, “Mechanical Dimensions of the TBGA Package,” for information on the package.

20.1 Package Parameters for the TBGA Package

The package parameters for rev. 2.0 silicon are as provided in the following list. The package type is 37.5 mm × 37.5 mm, 740 tape ball grid array (TBGA).

Package outline	37.5 mm × 37.5 mm
Interconnects	740
Pitch	1.00 mm
Module height (typical)	1.46 mm
Solder Balls	62 Sn/36 Pb/2 Ag (ZU package) 95.5 Sn/0.5 Cu/4Ag (VV package)
Ball diameter (typical)	0.64 mm

20.2 Mechanical Dimensions of the TBGA Package

This figure depicts the mechanical dimensions and bottom surface nomenclature of the device, 740-TBGA package.

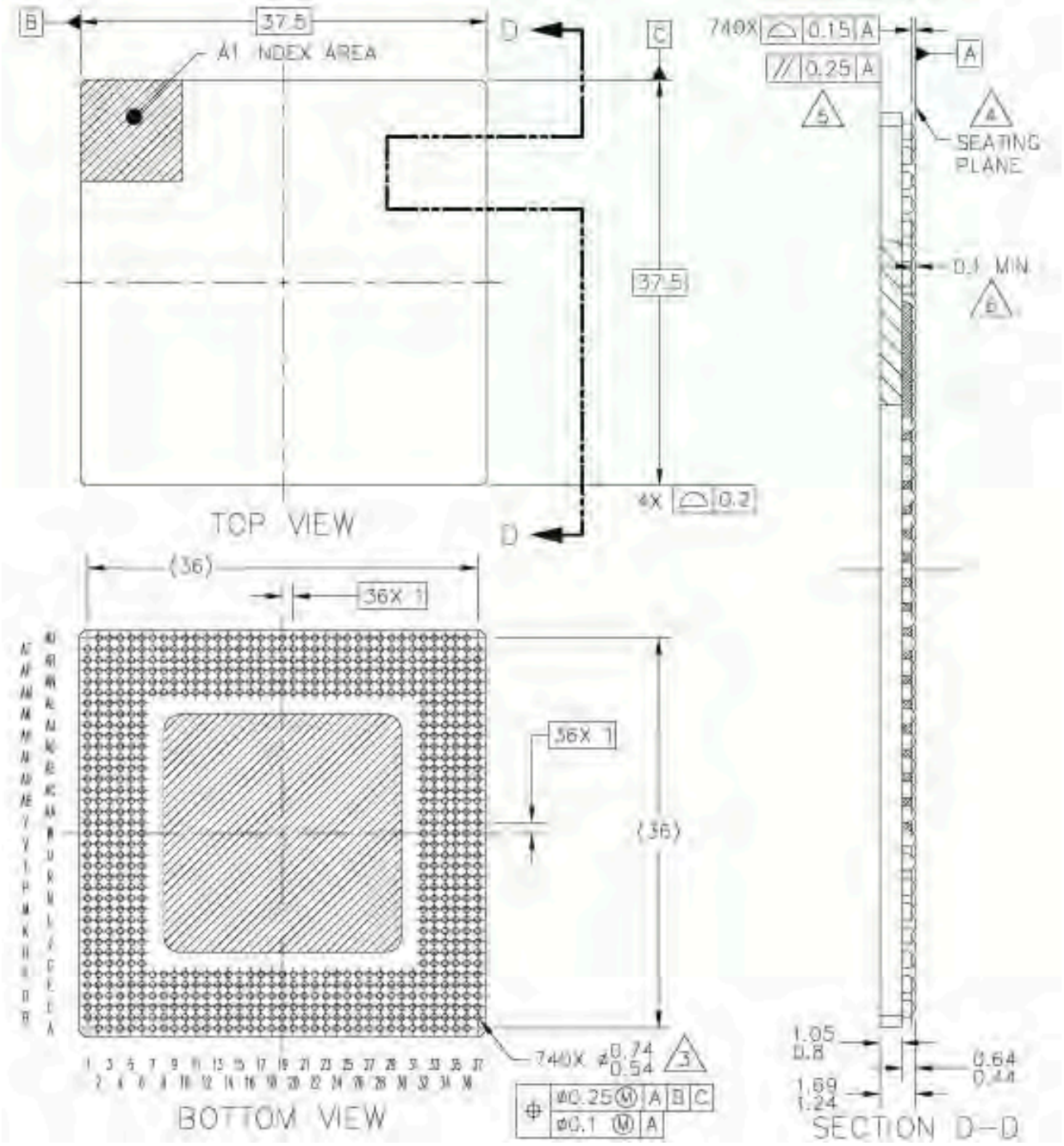

Figure 53. Mechanical Dimensions and Bottom Surface Nomenclature of the TBGA Package

20.3 Pinout Listings

Refer to AN3097, “MPC8360/MPC8358E PowerQUICC Design Checklist,” for proper pin termination and usage.

This table shows the pin list of the MPC8360E TBGA package.

Table 66. MPC8360E TBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Primary DDR SDRAM Memory Controller Interface				
MEMC1_MDQ[0:31]	AJ34, AK33, AL33, AL35, AJ33, AK34, AK32, AM36, AN37, AN35, AR34, AT34, AP37, AP36, AR36, AT35, AP34, AR32, AP32, AM31, AN33, AM34, AM33, AM30, AP31, AM27, AR30, AT32, AN29, AP29, AN27, AR29	I/O	GV_{DD}	—
MEMC1_MDQ[32:63]/ MEMC2_MDQ[0:31]	AN8, AN7, AM8, AM6, AP9, AN9, AT7, AP7, AU6, AP6, AR4, AR3, AT6, AT5, AR5, AT3, AP4, AM5, AP3, AN3, AN5, AL5, AN4, AM2, AL2, AH5, AK3, AJ2, AJ3, AH4, AK4, AH3	I/O	GV_{DD}	—
MEMC1_MECC[0:4]/ MSRCID[0:4]	AP24, AN22, AM19, AN19, AM24	I/O	GV_{DD}	—
MEMC1_MECC[5]/ MDVAL	AM23	I/O	GV_{DD}	—
MEMC1_MECC[6:7]	AM22, AN18	I/O	GV_{DD}	—
MEMC1_MDM[0:3]	AL36, AN34, AP33, AN28	O	GV_{DD}	—
MEMC1_MDM[4:7]/ MEMC2_MDM[0:3]	AT9, AU4, AM3, AJ6	O	GV_{DD}	—
MEMC1_MDM[8]	AP27	O	GV_{DD}	—
MEMC1_MDQS[0:3]	AK35, AP35, AN31, AM26	I/O	GV_{DD}	—
MEMC1_MDQS[4:7]/ MEMC2_MDQS[0:3]	AT8, AU3, AL4, AJ5	I/O	GV_{DD}	—
MEMC1_MDQS[8]	AP26	I/O	GV_{DD}	—
MEMC1_MBA[0:1]	AU29, AU30	O	GV_{DD}	—
MEMC1_MBA[2]	AT30	O	GV_{DD}	—
MEMC1_MA[0:14]	AU21, AP22, AP21, AT21, AU25, AU26, AT23, AR26, AU24, AR23, AR28, AU23, AR22, AU20, AR18	O	GV_{DD}	—
MEMC1_MODT[0:1]	AG33, AJ36	O	GV_{DD}	6
MEMC1_MODT[2:3]/ MEMC2_MODT[0:1]	AT1, AK2	O	GV_{DD}	6
$\overline{\text{MEMC1\_MWE}}$	AT26	O	GV_{DD}	—
$\overline{\text{MEMC1\_MRAS}}$	AT29	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCAS}}$	AT24	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCS}}$[0:1]	AU27, AT27	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCS}}$[2:3]/ $\overline{\text{MEMC2\_MCS}}$[0:1]	AU8, AU7	O	GV_{DD}	—

Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
CE_PA[22]	AF3	I/O	OV_{DD}	—
CE_PA[23:26]	C18, D18, E18, A18	I/O	$LV_{DD}1$	—
CE_PA[27:28]	AF2, AE6	I/O	OV_{DD}	—
CE_PA[29]	B19	I/O	$LV_{DD}1$	—
CE_PA[30]	AE5	I/O	OV_{DD}	—
CE_PA[31]	F16	I/O	$LV_{DD}1$	—
CE_PB[0:27]	AE2, AE1, AD5, AD3, AD2, AC6, AC5, AC4, AC2, AC1, AB5, AB4, AB3, AB1, AA6, AA4, AA2, Y6, Y4, Y3, Y2, Y1, W6, W5, W2, V5, V3, V2	I/O	OV_{DD}	—
CE_PC[0:1]	V1, U6	I/O	OV_{DD}	—
CE_PC[2:3]	C16, A15	I/O	$LV_{DD}1$	—
CE_PC[4:6]	U4, U3, T6	I/O	OV_{DD}	—
CE_PC[7]	C19	I/O	$LV_{DD}2$	—
CE_PC[8:9]	A4, C5	I/O	$LV_{DD}0$	—
CE_PC[10:30]	T5, T4, T2, T1, R5, R3, R1, C11, D12, F13, B10, C10, E12, A9, B8, D10, A14, E15, B14, D15, AH2	I/O	OV_{DD}	—
CE_PD[0:27]	E11, D9, C8, F11, A7, E9, C7, A6, F10, B6, D7, E8, B5, A5, C2, E4, F5, B1, D2, G5, D1, E2, H6, F3, E1, F2, G3, H4	I/O	OV_{DD}	—
CE_PE[0:31]	K3, J2, F1, G2, J5, H3, G1, H2, K6, J3, K5, K4, L6, P6, P4, P3, P1, N4, N5, N2, N1, M2, M3, M5, M6, L1, L2, L4, E14, C13, C14, B13	I/O	OV_{DD}	—
CE_PF[0:3]	F14, D13, A12, A11	I/O	OV_{DD}	—
Clocks				
PCI_CLK_OUT[0]/CE_PF[26]	B22	I/O	$LV_{DD}2$	—
PCI_CLK_OUT[1:2]/CE_PF[27:28]	D22, A23	I/O	OV_{DD}	—
CLKIN	E37	I	OV_{DD}	—
PCI_CLOCK/PCI_SYNC_IN	M36	I	OV_{DD}	—
PCI_SYNC_OUT/CE_PF[29]	D37	I/O	OV_{DD}	3
JTAG				
TCK	K33	I	OV_{DD}	—
TDI	K34	I	OV_{DD}	4
TDO	H37	O	OV_{DD}	3
TMS	J36	I	OV_{DD}	4
$\overline{\text{TRST}}$	L32	I	OV_{DD}	4
Test				
TEST	L35	I	OV_{DD}	7
TEST_SEL	AU34	I	GV_{DD}	7

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{IRQ}}$[4:5]	G33, G32	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[6]/$\overline{\text{LCS}}$[6]/$\overline{\text{CKSTOP\_OUT}}$	E35	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[7]/$\overline{\text{LCS}}$[7]/$\overline{\text{CKSTOP\_IN}}$	H36	I/O	OV_{DD}	—
DUART				
UART1_SOUT/M1SRCID[0]/ M2SRCID[0]/LSRCID[0]	E32	O	OV_{DD}	—
UART1_SIN/M1SRCID[1]/ M2SRCID[1]/LSRCID[1]	B34	I/O	OV_{DD}	—
$\overline{\text{UART1\_CTS}}$/M1SRCID[2]/ M2SRCID[2]/LSRCID[2]	C34	I/O	OV_{DD}	—
$\overline{\text{UART1\_RTS}}$/M1SRCID[3]/ M2SRCID[3]/LSRCID[3]	A35	O	OV_{DD}	—
I^2C Interface				
IIC1_SDA	D34	I/O	OV_{DD}	2
IIC1_SCL	B35	I/O	OV_{DD}	2
IIC2_SDA	E33	I/O	OV_{DD}	2
IIC2_SCL	C35	I/O	OV_{DD}	2
QUICC Engine				
CE_PA[0]	F8	I/O	LV_{DD0}	—
CE_PA[1:2]	AH1, AG5	I/O	OV_{DD}	—
CE_PA[3:7]	F6, D4, C3, E5, A3	I/O	$LV_{DD}0$	—
CE_PA[8]	AG3	I/O	OV_{DD}	—
CE_PA[9:12]	F7, B3, E6, B4	I/O	$LV_{DD}0$	—
CE_PA[13:14]	AG1, AF6	I/O	OV_{DD}	—
CE_PA[15]	B2	I/O	$LV_{DD}0$	—
CE_PA[16]	AF4	I/O	OV_{DD}	—
CE_PA[17:21]	B16, A16, E17, A17, B17	I/O	$LV_{DD}1$	—
CE_PA[22]	AF3	I/O	OV_{DD}	—
CE_PA[23:26]	C18, D18, E18, A18	I/O	$LV_{DD}1$	—
CE_PA[27:28]	AF2, AE6	I/O	OV_{DD}	—
CE_PA[29]	B19	I/O	$LV_{DD}1$	—
CE_PA[30]	AE5	I/O	OV_{DD}	—
CE_PA[31]	F16	I/O	$LV_{DD}1$	—

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
No Connect				
NC	AM16, AM17, AM20, AN13, AN16, AN17, AP10, AP11, AP13, AP15, AP18, AR11, AR13, AR14, AR15, AR16, AR17, AR20, AT11, AT12, AT13, AT14, AT16, AT17, AT18, AU10, AU11, AU12, AU13, AU15, AU19	—	—	—

Notes:

1. This pin is an open drain signal. A weak pull-up resistor (1 kΩ) should be placed on this pin to OV_{DD}.
2. This pin is an open drain signal. A weak pull-up resistor (2–10 kΩ) should be placed on this pin to OV_{DD}.
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow PCI specifications recommendation.
6. These are On Die Termination pins, used to control DDR2 memories internal termination resistance.
7. This pin must always be tied to GND.
8. This pin must always be left not connected.
9. Refer to *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* section on “RGMII Pins,” for information about the two UCC2 Ethernet interface options.
10. This pin must always be tied to GV_{DD}.
11. It is recommended that MDIC0 be tied to GND using an 18.2 Ω resistor and MDIC1 be tied to DDR power using an 18.2 Ω resistor for DDR2.

21 Clocking

This figure shows the internal distribution of clocks within the MPC8360E.

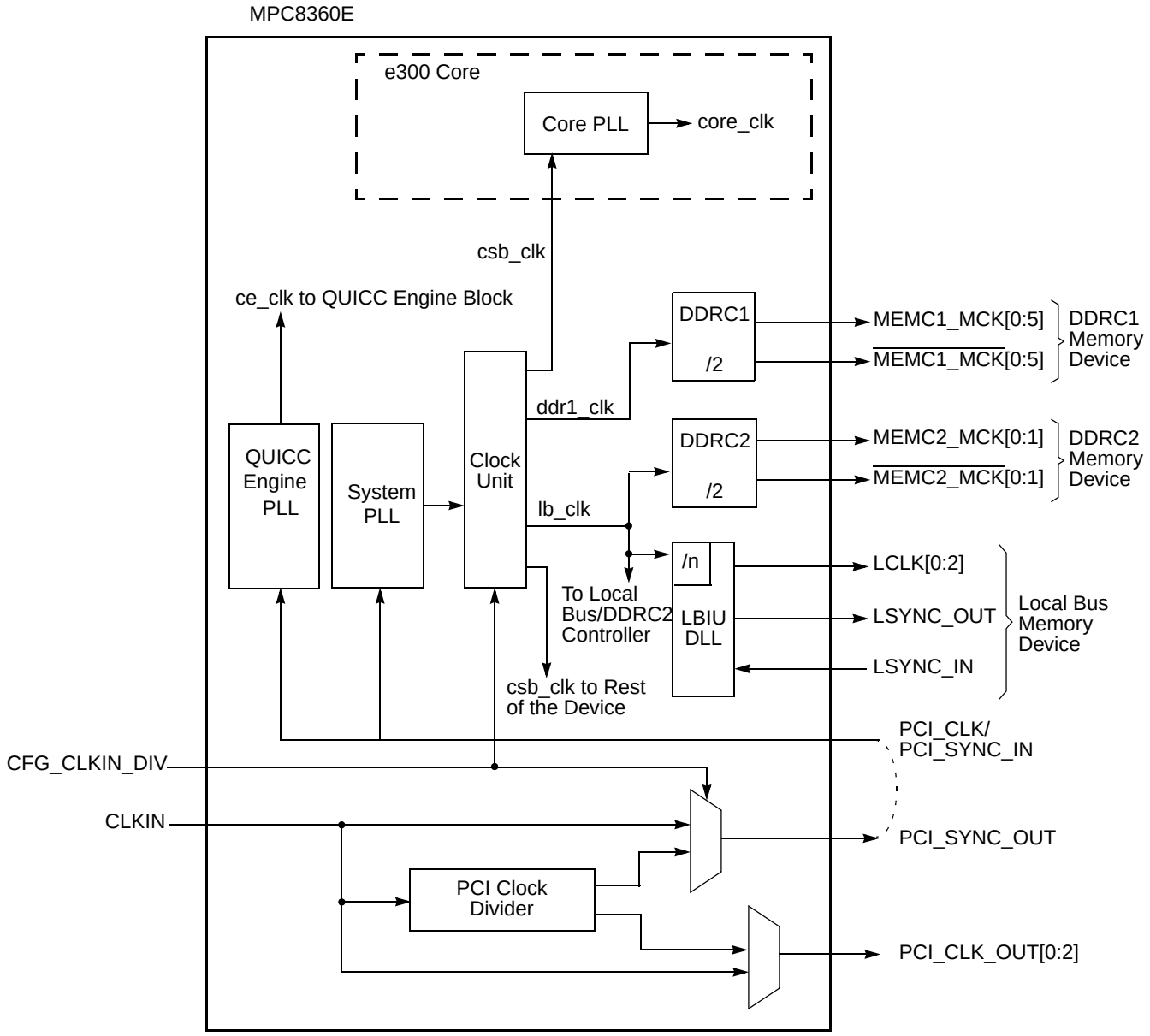

Figure 54. MPC8360E Clock Subsystem

This table shows heat sinks and junction-to-ambient thermal resistance for TBGA package.

Table 78. Heat Sinks and Junction-to-Ambient Thermal Resistance of TBGA Package

Heat Sink Assuming Thermal Grease	Airflow	35 × 35 mm TBGA
		Junction-to-Ambient Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convention	10.7
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	6.2
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	5.3
AAVID 31 × 35 × 23 mm pin fin	Natural convention	8.1
AAVID 31 × 35 × 23 mm pin fin	1 m/s	4.4
AAVID 31 × 35 × 23 mm pin fin	2 m/s	3.7
Wakefield, 53 × 53 × 25 mm pin fin	Natural convention	5.4
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	3.2
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	2.4
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convention	6.4
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	3.8
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	2.5
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	2.8

Accurate thermal design requires thermal modeling of the application environment using computational fluid dynamics software which can model both the conduction cooling and the convection cooling of the air moving through the application. Simplified thermal models of the packages can be assembled using the junction-to-case and junction-to-board thermal resistances listed in the thermal resistance table. More detailed thermal models can be made available on request.

Heat sink vendors include the following:

Aavid Thermalloy 603-224-9988
80 Commercial St.
Concord, NH 03301
Internet: www.aavidthermalloy.com

Alpha Novatech 408-749-7601
473 Sapena Ct. #15
Santa Clara, CA 95054
Internet: www.alphanovatech.com

International Electronic Research Corporation (IERC) 818-842-7277
413 North Moss St.
Burbank, CA 91502
Internet: www.ctscorp.com

Table 82. Revision History (continued)

Rev. Number	Date	Substantive Change(s)
3	03/2010	• Changed references to RCWH[PCICKEN] to RCWH[PCICKDRV]. • In Table 2, added extended temperature characteristics. • Added Figure 6, “DDR Input Timing Diagram.” • In Figure 53, “Mechanical Dimensions and Bottom Surface Nomenclature of the TBGA Package,” removed watermark. • Updated the title of Table 19,”DDR SDRAM Input AC Timing Specifications.” • In Table 20, “DDR and DDR2 SDRAM Input AC Timing Specifications Mode,” changed table subtitle. • In Table 27–Table 30, and Table 33—Table 34, changed the rise and fall time specifications to reference 20–80% and 80–20% of the voltage supply, respectively. • In Table 38, “IEEE 1588 Timer AC Specifications,” changed first parameter to “Timer clock frequency.” • In Table 45, “I2C AC Electrical Specifications,” changed units to “ns” for t_{I2DVKH}. • In Table 66, “MPC8360E TBGA Pinout Listing,” and Table 67 “MPC8358E TBGA Pinout Listing, added note 7: “This pin must always be tied to GND” to the TEST pin and added a note to SPARE1 stating: “This pin must always be left not connected.” • In Section 4, “Clock Input Timing,” added note regarding rise/fall time on QUICC Engine block input pins. • Added Section 4.3, “Gigabit Reference Clock Input Timing.” • Updated Section 8.1.1, “10/100/1000 Ethernet DC Electrical Characteristics.” • In Section 20.3, “Pinout Listings,” added sentence stating “Refer to AN3097, ‘MPC8360/MPC8358E PowerQUICC Design Checklist,’ for proper pin termination and usage.” • In Section 21, “Clocking,” removed statement: “The OCCR[PCICDn] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUTn signals.” • In Section 21.1, “System PLL Configuration,” updated the system VCO frequency conditions. • In Table 80, added extended temperature characteristics.
2	12/2007	Initial release.